

NTE552 Silicon Rectifier General Purpose, Fast Recovery

Features:

- Low Cost
- Low Leakage
- Low Forward Voltage Drop
- High Current Capability
- Supplied in DO41 Package

Maximum Ratings and Electrical Characteristics:

(Ratings at 26°C ambient temperature unless otherwise noted. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%)

Maximum Recurrent Peak Reverse Voltage	600V
Maximum RMS Voltage	420V
Maximum DC Blocking Voltage	600V
Maximum Average Forward Rectified Current (.375" (9.5mm) Lead Length at $T_A = +75^\circ\text{C}$)	1A
Peak Forward Surge Current (8.3ms Single Half Sine-Wave Superimposed on Rated Load)	50A
Maximum Instantaneous Forward Voltage at 1A DC	1.2V
Maximum DC Reverse Current at Rated DC Blocking Voltage ($T_A = +25^\circ\text{C}$)	5.0 μA
Maximum Full Load Reverse Current (Full Cycle Average (.375" (9.5mm) Lead Length at $T_L = +55^\circ\text{C}$)	100 μA
Maximum Reverse Recovery Time (Note 1)	200nS
Typical Junction Capacitance (Note 2)	15pF
Operating Junction Temperature Range, T_J	-65° to $+175^\circ\text{C}$
Storage Temperature Range, T_{stg}	-65° to $+175^\circ\text{C}$

Note 1. Reverse Recovery Test Conditions: $I_F = 1\text{A}$, $V_R = 30\text{V}$

Note 2. Measured at 1MHz and applied reverse voltage of 4 volts.

